

12-bit 1-channel 25 MSPS pipeline ADC

SPECIFICATION

1 FEATURES

- iHP SiGe BiCMOS 0.25 μm
- Resolution 12 bit
- Sampling frequency 15 to 25 MHz
- Low power consumption in standby mode
- Low power dissipation (125 mW)
- Signal-to-noise ratio (SNR) 61 dB
- Spurious-free dynamic range (SFDR) 62 dB
- Portable to other technologies (upon request)

2 APPLICATION

- Optical networking
- Test equipment
- Portable ultrasound and digital beam-forming systems
- Telecommunication systems
- Higher quality imaging in video systems

3 OVERVIEW

The low-power high-speed 12-bit ADC employs high-performance differential pipeline architecture.

The ADC consists of a sample and hold device, a core ADC and block of comparators. The ADC requires: 2.5 V analog supply, differential reference voltages 1.5 V and 1.0 V, common mode voltage 0.75 V and differential input clock.

The ADC supports standby mode which allows state with minimum power consumption.

There is also the ability to configure the operating modes of the ADC by using digital registers.

The block is fabricated on iHP SiGe BiCMOS 0.25 μm technology.

4 STRUCTURE

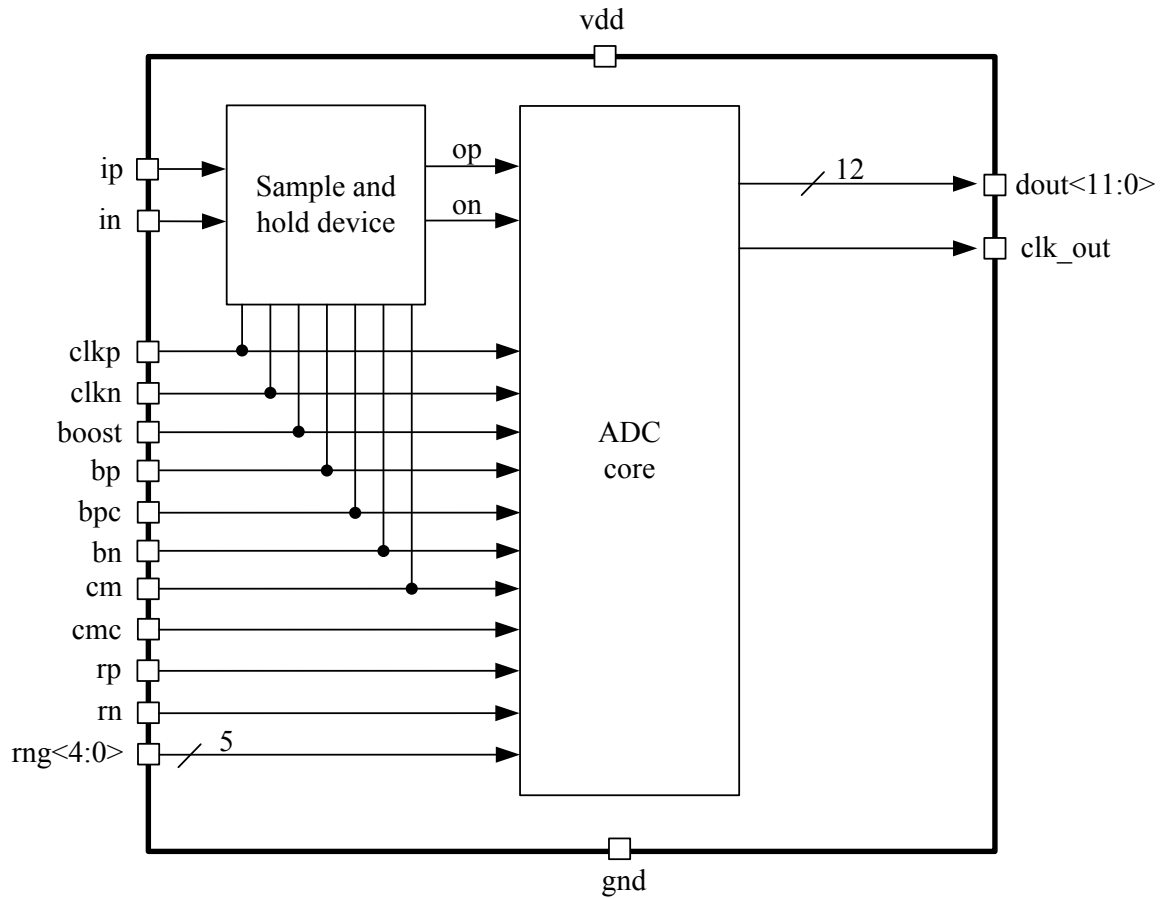


Figure 1: 12-bit 1-channel 25 MSPS pipeline ADC structure

5 PIN DESCRIPTION

Name	Direction	Description
ip	I	Analog differential input
in		
clkp	I	Differential input clock signal
clkn		
boost	I	Reference level for keys block
bp	I	Reference level for current sources
bpc	I	Reference level for current sources
bn	I	Reference level for current sources
cm	I	Average level of the reference voltage
cmc	I	Reference level for comparators
rp	I	High level reference voltage
rn	I	Low level reference voltage
rng<4:0>	I	Comparators selection register (1/8 or 3/8)
dout<11:0>	O	Output data signal
clk_out	O	Output clk signal
vdd	I/O	Supply voltage 2.5 V
gnd	I/O	Ground bus

6 LAYOUT DESCRIPTION

Analog-to-digital converter layout dimensions are given in the table 1.

Table 1: Block dimensions of the 12-bit ADC

Dimension	Value	Unit
Height	2280	μm
Width	340	μm

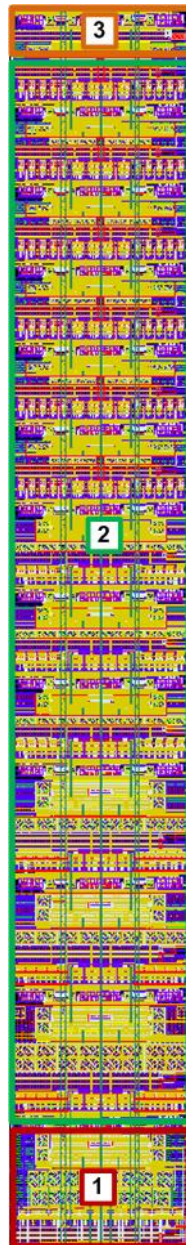


Figure 2: 12-bit ADC layout view

1. Sample and hold device
2. Block of multiplying DACs
3. Block of comparators

7 OPERATING CHARACTERISTICS

7.1 TECHNICAL CHARACTERISTICS

Technology _____ iHP SiGe BiCMOS 0.25 um
 Status _____ silicon proven
 Area _____ 0.8 mm²

7.2 ELECTRICAL CHARACTERISTICS

The values of electrical characteristics are specified for $V_{dd}=2.25\pm 2.75V$, $T = -60\pm 125^{\circ}C$. Typical values are $V_{dd} = 2.5V$, $T = +27^{\circ}C$, unless otherwise specified.

Parameter	Symbol	Condition	Value			Unit
			min	typ.	max	
Supply voltage	V_{dd}	-	2.25	2.5	2.75	V
Operating temperature range	T	-	-60	27	+125	°C
Resolution	N	-	-	12	-	bit
Standby current	I_{st}	-	-	60	-	uA
Current consumption	I_{cc}	-	-	50	-	mA
Maximum input amplitude	A_{IN}	-	-	0.5	-	V
Bandwidth	B	-	7.5	10.0	12.5	MHz
Sampling rate	F_s	-	15	20	25	MSPS
Input reference voltage	V_{REF+}	-	-	1.5	-	V
	V_{REF-}		-	1	-	V
Peak-to-peak differential input voltage	$A_{IN\ p-p}$	-	-	1	-	V
DC operating point	U	-	$0.5V_{dd}$ -100mV	$0.5V_{dd}$	$0.5V_{dd}$ +100mV	V
Signal-noise ratio	SNR	Input amplitude $0.9 A_{IN}$, input frequency 1.5 MHz, $F_{clk} = 20$ MHz	-	61	-	dB
Spurious-free dynamic range	SFDR		56	62	64	dB
Input logic-level high	V_{IH}	For digital inputs	$0.7V_{dd}$	-	$V_{dd}+0.25$	V
Input logic-level low	V_{IL}		-0.25	-	0.3	V

8 DELIVERABLES

Depending on license type IP may include:

- Schematic or NetList
- Abstract view (.lef and .lib files)
- Layout (optional)
- Verilog behavior model
- Extracted view (optional)
- GDSII
- DRC, LVS, antenna report
- Test bench with saved configurations (optional)
- Documentation

REVISION HISTORY

From version 1.1:

- Section 1 updated
- Section 3 updated
- Subsection 7.2 updated